Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic level compatible
- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- · Relay driver
- · High-speed line driver
- · High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|------|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | -70 | V |
| V_{GS} | gate-source voltage | | | -20 | - | 20 | V |
| I _D | drain current | V_{GS} = -10 V; T_{amb} = 25 °C | [1] | - | - | -2.4 | Α |
| Static characte | Static characteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = -10 V; I_D = -2.4 A; T_j = 25 °C | | - | 130 | 167 | mΩ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|----------------------------|--|
| 1 | G | gate | 4 | D |
| 2 | D | drain | | |
| 3 | S | source | | G \downarrow \downarrow \downarrow |
| 4 | D | drain | ⊟1 ⊟2 ⊟3 SC-73 (SOT223) | S 017aaa259 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|---------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PMT200EPE | SC-73 | plastic surface-mounted package with increased heatsink; 4 leads | SOT223 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMT200EPE | T2EPE |

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|---|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | -70 | V |
| V _{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = -10 V; T _{amb} = 25 °C | [1] | - | -2.4 | Α |
| | | V _{GS} = -10 V; T _{amb} = 100 °C | [1] | - | -1.5 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | -9.7 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 800 | mW |
| | | | [1] | - | 1.75 | W |
| | | T _{sp} = 25 °C | | - | 8.3 | W |
| T _j | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $T_{j(init)}$ = 25 °C; I_D = -1.3 A; DUT in avalanche (unclamped) | | - | 19.5 | mJ |
| Source-drain | n diode | | ' | | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | -1.8 | Α |
| ESD maximu | um rating | | ' | ' | ' | |
| V _{ESD} | electrostatic discharge voltage | НВМ | [3] | - | 2000 | V |

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Measured between all pins.

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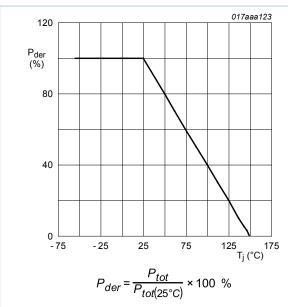


Fig. 1. Normalized total power dissipation as a function of junction temperature

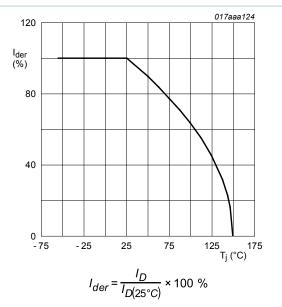
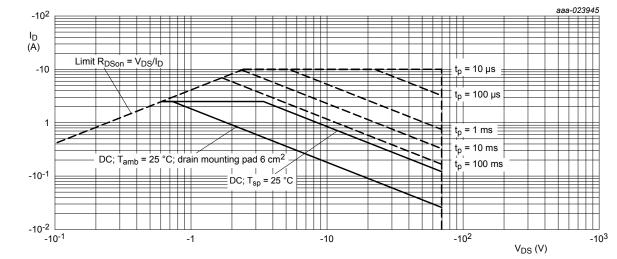


Fig. 2. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

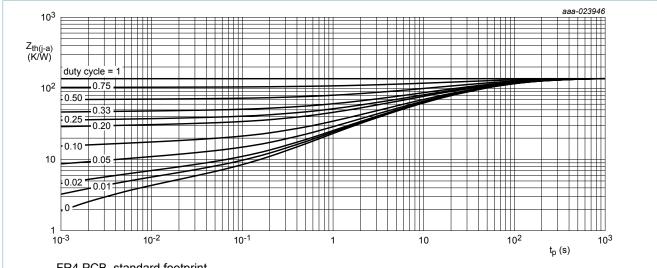
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9. Thermal characteristics

Table 6. Thermal characteristics

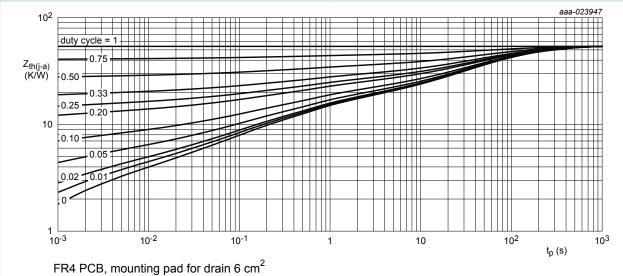
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | - | [1] | - | 135 | 155 | K/W |
| | | | [2] | - | 54 | 70 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 7 | 15 | K/W |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 5.

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|---|-----|------|------|------|
| Static char | acteristics | | ' | ' | | , |
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | -70 | - | - | V |
| V_{GSth} | gate-source threshold voltage | I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C | -1 | -2 | -3 | V |
| I _{DSS} | drain leakage current | $V_{DS} = -70 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | - | -1 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μA |
| | | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | - | -10 | μA |
| | | V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 2 | μA |
| | | V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -2 | μA |
| R _{DSon} | drain-source on-state | V_{GS} = -10 V; I_D = -2.4 A; T_j = 25 °C | - | 130 | 167 | mΩ |
| | resistance | V _{GS} = -10 V; I _D = -2.4 A; T _j = 150 °C | - | 234 | 250 | mΩ |
| | | V_{GS} = -4.5 V; I_D = -2.1 A; T_j = 25 °C | - | 150 | 225 | mΩ |
| 9 _{fs} | forward transconductance | V_{DS} = -10 V; I_{D} = -2.4 A; T_{j} = 25 °C | - | 13.5 | - | S |
| R _G | gate resistance | f = 1 MHz | - | 12 | - | Ω |
| Dynamic c | haracteristics | | ' | | | _ |
| Q _{G(tot)} | total gate charge | $V_{DS} = -35 \text{ V}; I_D = -2.4 \text{ A}; V_{GS} = -10 \text{ V};$ | - | 10.6 | 15.9 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 2.2 | - | nC |
| Q_{GD} | gate-drain charge | | - | 1.05 | - | nC |
| C _{iss} | input capacitance | V _{DS} = -35 V; f = 1 MHz; V _{GS} = 0 V; | - | 822 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 47 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 31.5 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = -35 \text{ V}; I_D = -2.4 \text{ A}; V_{GS} = -10 \text{ V};$ | - | 6 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 8 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 42 | - | ns |
| t _f | fall time | | - | 20 | - | ns |
| Source-dra | ain diode | | ' | | , | |
| V_{SD} | source-drain voltage | I _S = -2.4 A; V _{GS} = 0 V; T _i = 25 °C | - | -0.8 | -1.2 | V |

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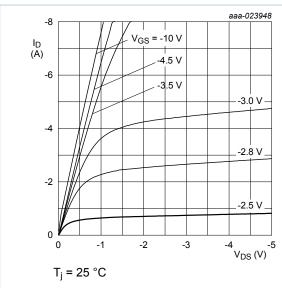


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

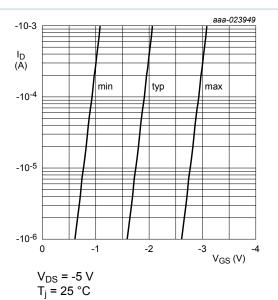


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

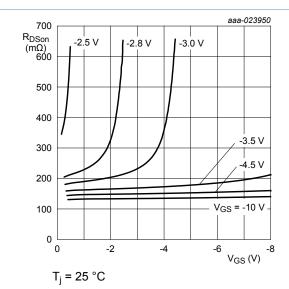


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

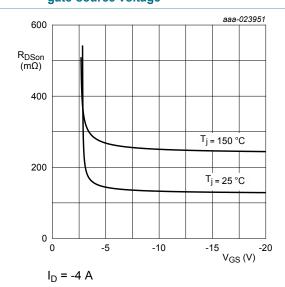


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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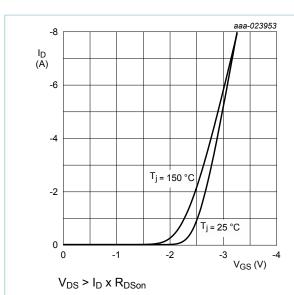


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

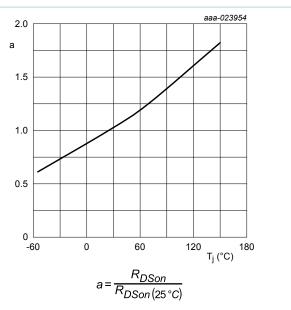


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

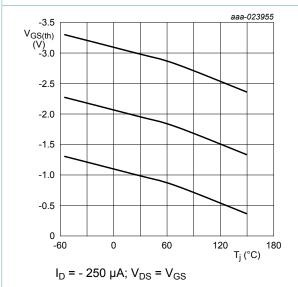


Fig. 12. Gate-source threshold voltage as a function of junction temperature

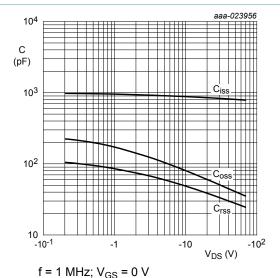
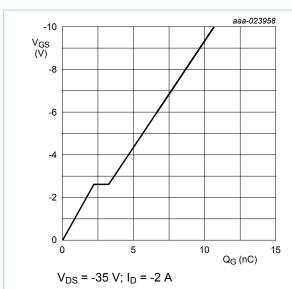


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V_{DS} — J_D V_{GS(pl)} V_{GS(th)} V_{GS} — Q_{GS} — Q_{GD} — Q_{GS} — Q_{G(tot)} — 003aaa508

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

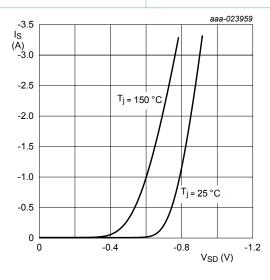
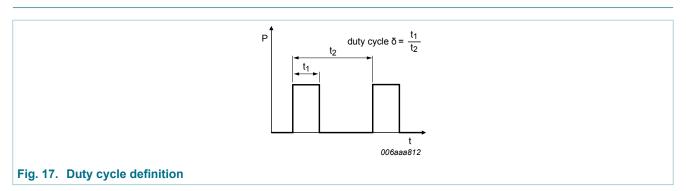


Fig. 16. Source current as a function of source-drain voltage; typical values

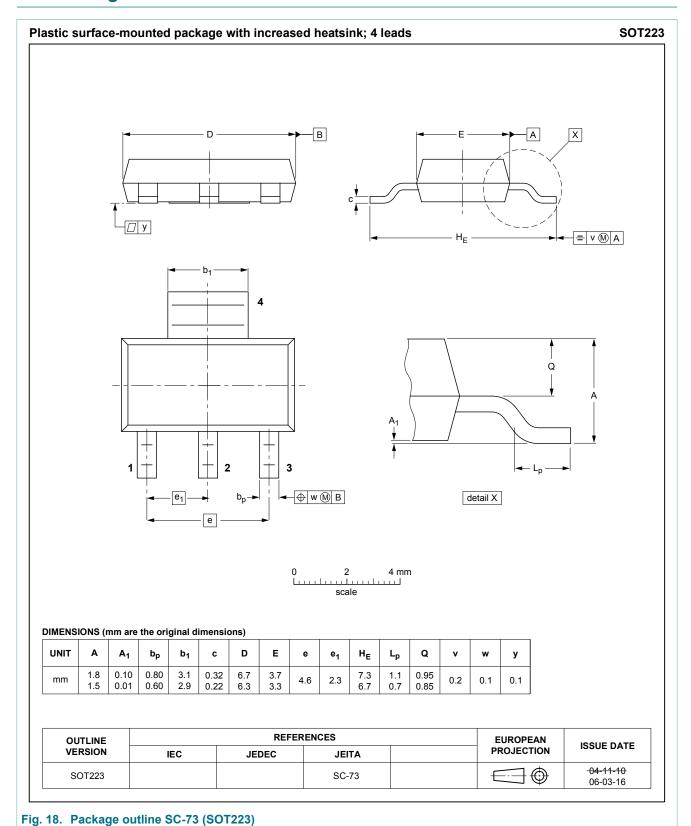
11. Test information

 $V_{GS} = 0 V$



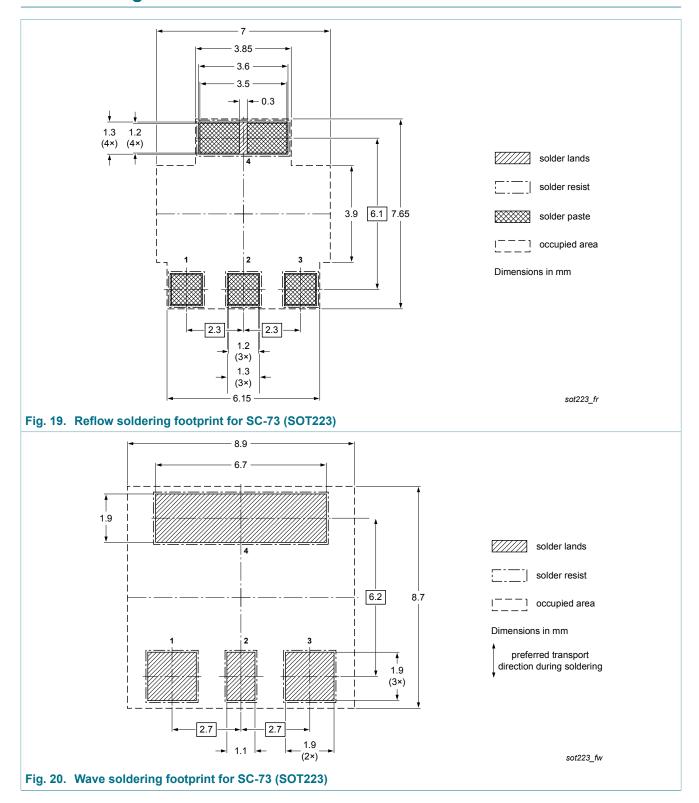
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMT200EPE v.1 | 20180314 | Product data sheet | - | - |

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15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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| Product [short] data sheet | Production | This document contains the product specification. |

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